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	Filing Date		2010-04-17	
	First Named Inventor	Michael D. Craven		
	Art Unit	2818		
	Examiner Name	Brandon C. Fox		
Attorney Docket Number		30794104USWO		

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	3	CRAVEN, Michael D., et. al., "Characterization of a-plane GaN/(Al,Ga)N multiple quantum wells grown via metalorganic chemical vapor deposition", JAPANESE JOURNAL OF APPLIED PHYSICS, PART 2 (LETTERS) JAPAN SOC. APPL. PHYS. JAPAN, vol. 42, no. 3A, March 1, 2003, pages L235-L238, XP002614887.	<input type="checkbox"/>
	4	CHEN, Changqing et. al., "Ultraviolet light emitting diodes using non-polar a-plane GaN-AlGaIn multiple quantum wells", JAPANESE JOURNAL OF APPLIED PHYSICS, PART 2 (LETTERS) JAPAN SOC. APPL. PHYS. JAPAN, vol. 42, no. 9AB, September 15, 2003, pages L1039-L1040, XP002614886.	<input type="checkbox"/>
	5	KUOKSTIS, E., et. al., "Polarization effects in photoluminescence of C- and M-plane GaN/AlGaIn multiple quantum wells", APPLIED PHYSICS LETTERS, AIP, AMERICAN INSTITUTE OF PHYSICS, Melville, NY, US., vol. 81, no. 22, November 25, 2002, pages 4130-4132, XP012032618.	<input type="checkbox"/>
	6	NG, H.M., "Molecular-beam epitaxy of GaN/AlxGa1-xN multiple quantum wells on R-plane (1012) sapphire substrates", APPLIED PHYSICS LETTERS, AIP, AMERICAN INSTITUTE OF PHYSICS, Melville, NY, vol. 80, no. 23, June 10, 2002, pages 4369-4371, XP012031145, ISSN: 0003-6951.	<input type="checkbox"/>
	7	SUN, W.H., et. al., "Strong ultraviolet emission from non-polar AlGaIn/GaN quantum wells grown over r-plane sapphire substrates", PHYSICA STATUS SOLIDI A WILEY-VCH GERMANY, vol. 200, no. 1, November 2003, pages 48-51, XP002614885, ISSN: 0031-8965.	<input type="checkbox"/>

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